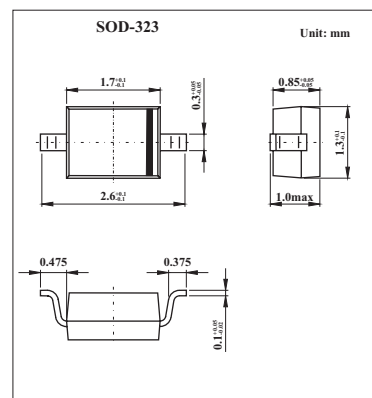


Silicon Epitaxial Planar Diode

KDV262

■ Features

- High Capacitance Ratio : $C_{2V}/C_{25V}=12.5(\text{Typ.})$
- Low Series Resistance : $r_s=0.6\ \Omega$ (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	34	V
Peak Reverse Voltage	V_{RM}	35 ($R_L=10K\ \Omega$)	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1\ \mu\text{A}$	34			V
Reverse Current	I_R	$V_R = 28\text{ V}$			10	nA
Capacitance	C_{2V}	$f = 1\text{ MHz}; V_R = 2\text{ V}$	33	35.5	38	pF
	C_{25V}	$f = 1\text{ MHz}; V_R = 25\text{ V}$	2.6	2.85	3.0	
Capacitance Ratio	C_{2V}/C_{25V}		12	12.5		
	C_{25V}/C_{28V}		1.03			
Series Resistance	r_s	$V_R = 5\text{ V}, f = 470\text{ MHz}$		0.6	0.8	Ω

Note :

Available in matched group for capacitance to 2.0%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.02$$

($V_R=2\sim 25\text{V}$)

■ Marking

Marking	UQ
---------	----